

**AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

**LISTING OF CLAIMS**

1. (Currently Amended) A semiconductor polishing composition comprising:

fumed silica as abrasive grains, the fumed silica having a bulk density of 50 g/L or more and less than 100 g/L;

~~the semiconductor polishing composition being obtained by preparing a mixture of an acidic aqueous solution~~ solution; ~~and fumed silica having a bulk density of 50 g/L or more and less than 100 g/L, and~~

an alkali aqueous solution; and so that pH of the mixture is in a range of 1 to 3  
~~and pH of the alkali aqueous solution is in a range of 12 to 14, and adding the mixture to the alkali aqueous solution continuously or intermittently;~~

coarse particles of approximately 0.5  $\mu$ m in diameter, the number of coarse particles being less than 140,000/0.5 ml, wherein the alkali aqueous solution contains at least one ~~or two or more additives~~ additive selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.

2. (Original) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.

- 3.-6. (Cancelled)

7. (Currently Amended) The semiconductor polishing composition of claim 1,  
wherein ~~alkali contained in the alkali aqueous solution is~~includes at least one or two or more  
~~hydroxides~~hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline  
earth metal hydroxide.

8. (Cancelled)

9. (Currently Amended) The semiconductor polishing composition of claim 2,  
wherein ~~alkali contained in the alkali aqueous solution is~~includes at least one or two or more  
~~hydroxides~~hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline  
earth metal hydroxide.

10.-11. (Cancelled)